

## 2329S-VB SOT23-3 Datasheet

### P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ.)
- 100	0.50 at $V_{GS} = - 10$ V	- 1.5	7.7
	0.56 at $V_{GS} = - 6.0$ V	- 1.4	

#### FEATURES

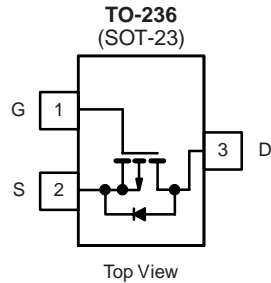
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET<sup>®</sup> Power MOSFET
- Ultra Low On-Resistance
- Small Size



**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**  
 Available

#### APPLICATIONS

- Active Clamp Circuits in DC/DC Power Supplies



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	- 100		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150$ °C) <sup>a, b</sup>	$I_D$	$T_A = 25$ °C	- 1.65	- 1.5
		$T_A = 70$ °C	- 1.55	- 1.4
Pulsed Drain Current	$I_{DM}$	- 3.0		A
Continuous Source Current (Diode Conduction) <sup>a, b</sup>	$I_S$	- 1.4	- 1.0	
Single Pulse Avalanche Current	$I_{AS}$	4.5		mJ
Single Pulse Avalanche Energy		$E_{AS}$	1.01	
Maximum Power Dissipation <sup>a, b</sup>	$P_D$	$T_A = 25$ °C	2.0	0.85
		$T_A = 70$ °C	1.0	0.58
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	75	100	°C/W	
		Steady State	120		
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	40	50		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.

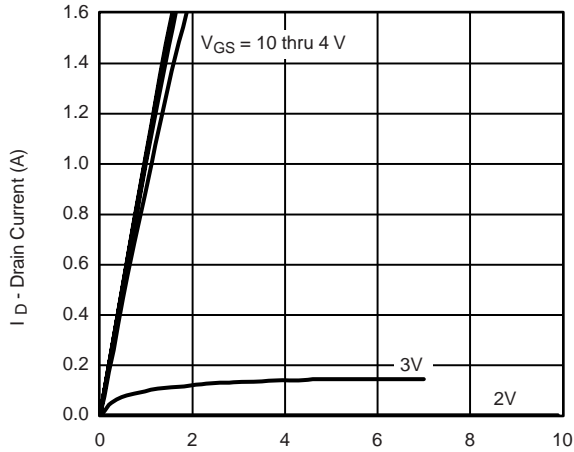
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 100			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1.0		- 3.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$			- 1	$\mu\text{A}$
		$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq -15\text{ V}, V_{GS} = 10\text{ V}$	- 1.6			A
Drain-Source On-Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -0.5\text{ A}$		0.50		$\Omega$
		$V_{GS} = -6.0\text{ V}, I_D = -0.5\text{ A}$		0.56		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -15\text{ V}, I_D = -0.5\text{ A}$		2.2		S
Diode Forward Voltage	$V_{SD}$	$I_S = -1.0\text{ A}, V_{GS} = 0\text{ V}$		0.7	- 1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = -50\text{ V}, V_{GS} = 10\text{ V},$ $I_D \cong -0.5\text{ A}$		7.7	12	nC
Gate-Source Charge	$Q_{gs}$			1.5		
Gate-Drain Charge	$Q_{gd}$			2.5		
Gate Resistance	$R_g$	$f = 1.0\text{ MHz}$		9		$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		520		pF
Output Capacitance	$C_{oss}$			40		
Reverse Transfer Capacitance	$C_{rss}$			20		
<b>Switching<sup>c</sup></b>						
Turn-On Time	$t_{d(on)}$	$V_{DD} = -50\text{ V}, R_L = 75\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -10\text{ V}$ $R_g = 6\text{ }\Omega$		7	11	ns
	$t_r$			11	17	
Turn-Off Time	$t_{d(off)}$			16	25	
	$t_f$			11	17	
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 0.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		90	135	nC

Notes:

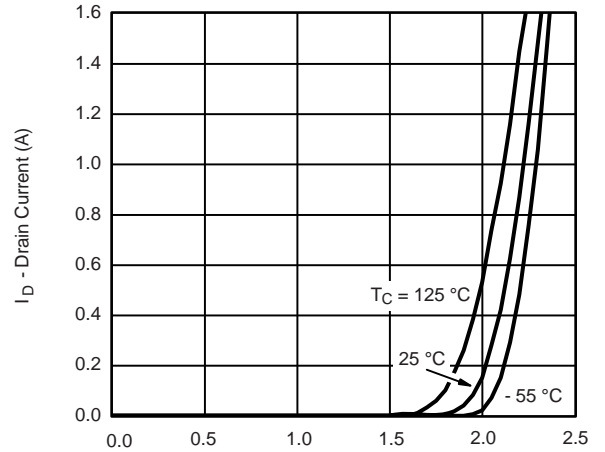
- a. Pulse test:  $PW \leq 300\text{ }\mu\text{s}$  duty cycle  $\leq 2\%$ .  
 b. For DESIGN AID ONLY, not subject to production testing.  
 c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

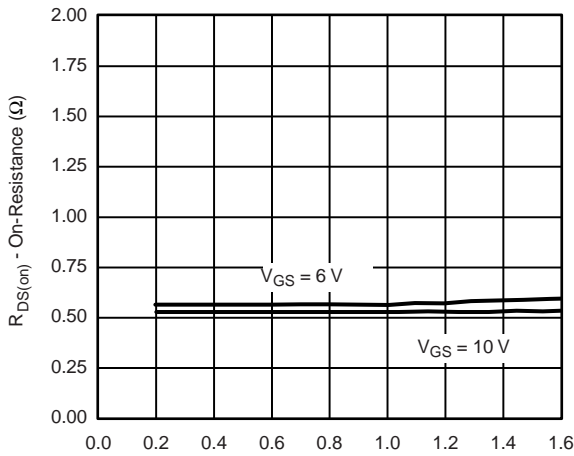
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



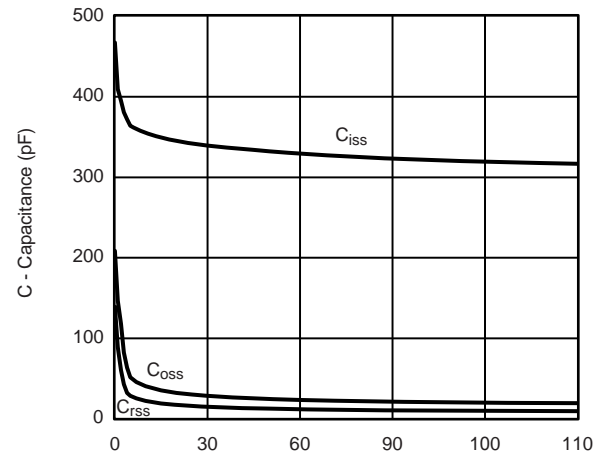
$V_{DS}$  - Drain-to-Source Voltage (V)  
**Output Characteristics**



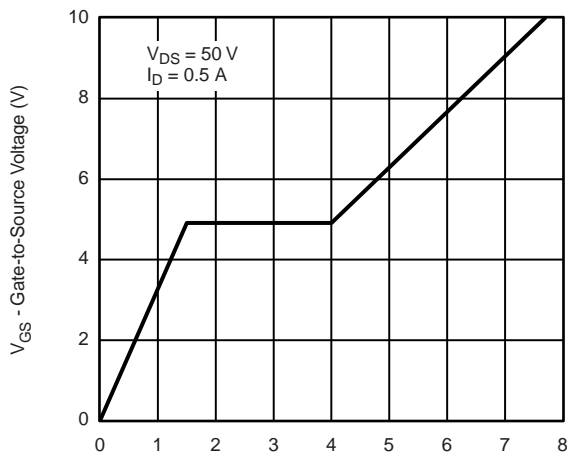
$V_{GS}$  - Gate-to-Source Voltage (V)  
**Transfer Characteristics**



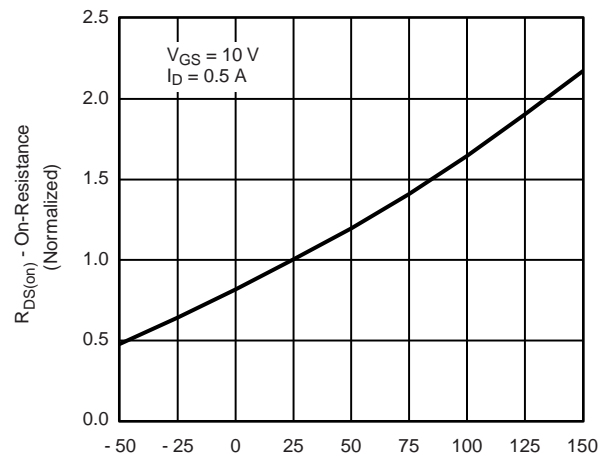
$I_D$  - Drain Current (A)  
**On-Resistance vs. Drain Current**



$V_{DS}$  - Drain-to-Source Voltage (V)  
**Capacitance**

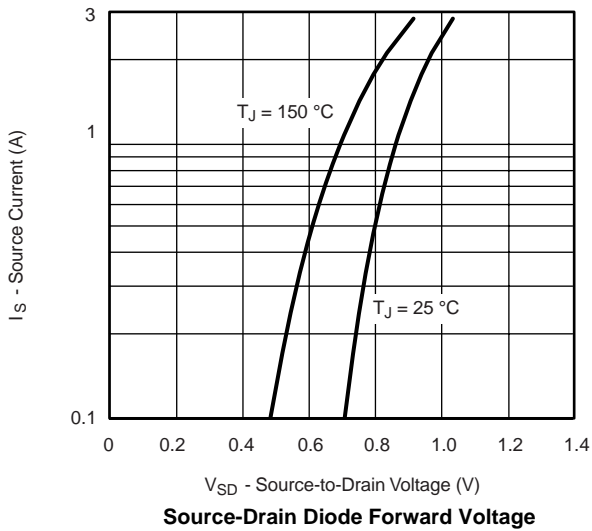


$Q_g$  - Total Gate Charge (nC)  
**Gate Charge**

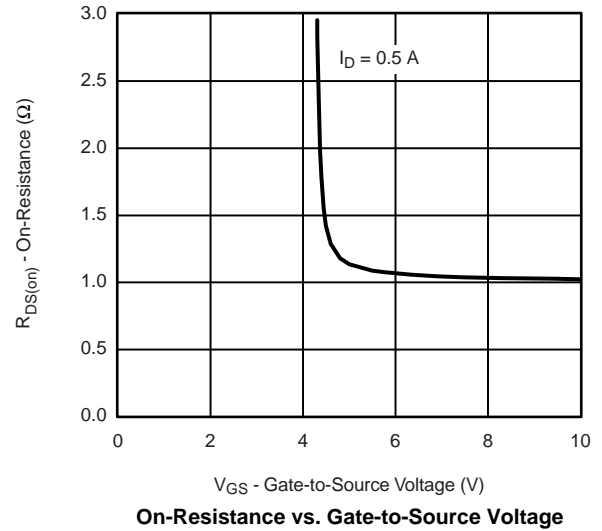


$T_J$  - Junction Temperature ( $^{\circ}C$ )  
**On-Resistance vs. Junction Temperature**

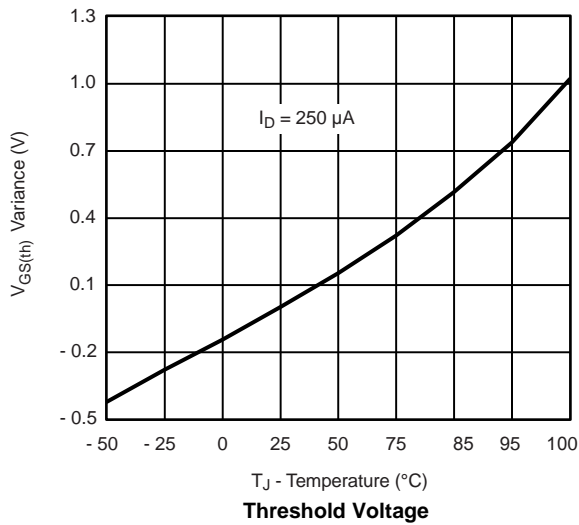
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



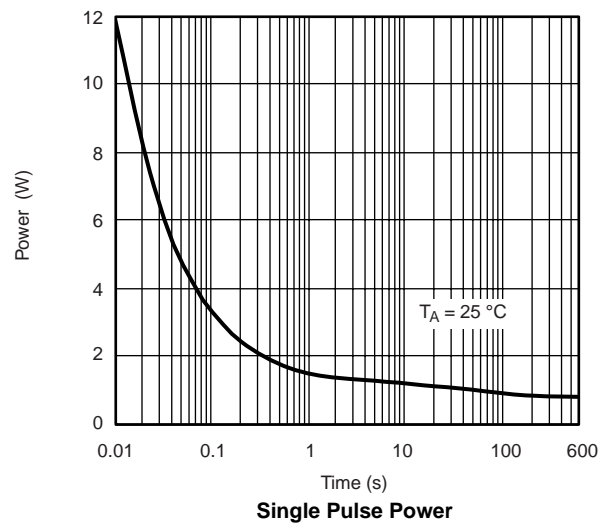
Source-Drain Diode Forward Voltage



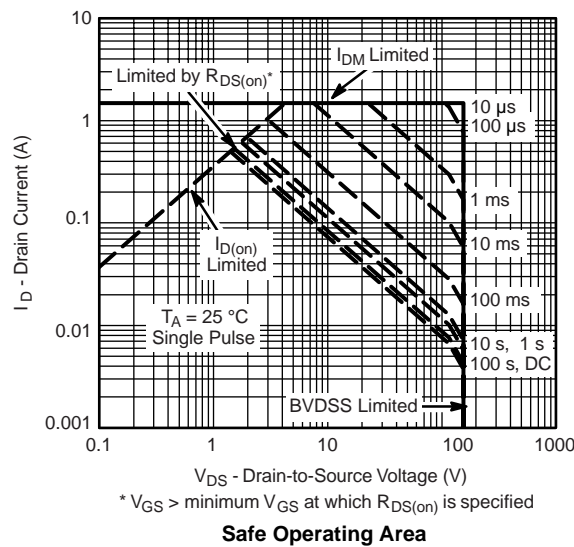
On-Resistance vs. Gate-to-Source Voltage



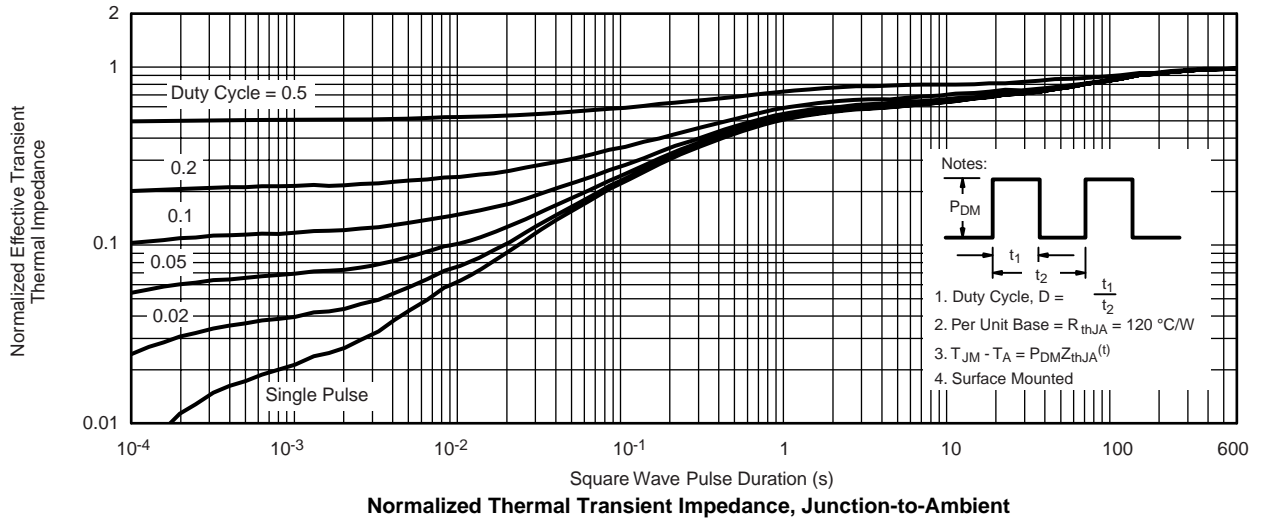
Threshold Voltage



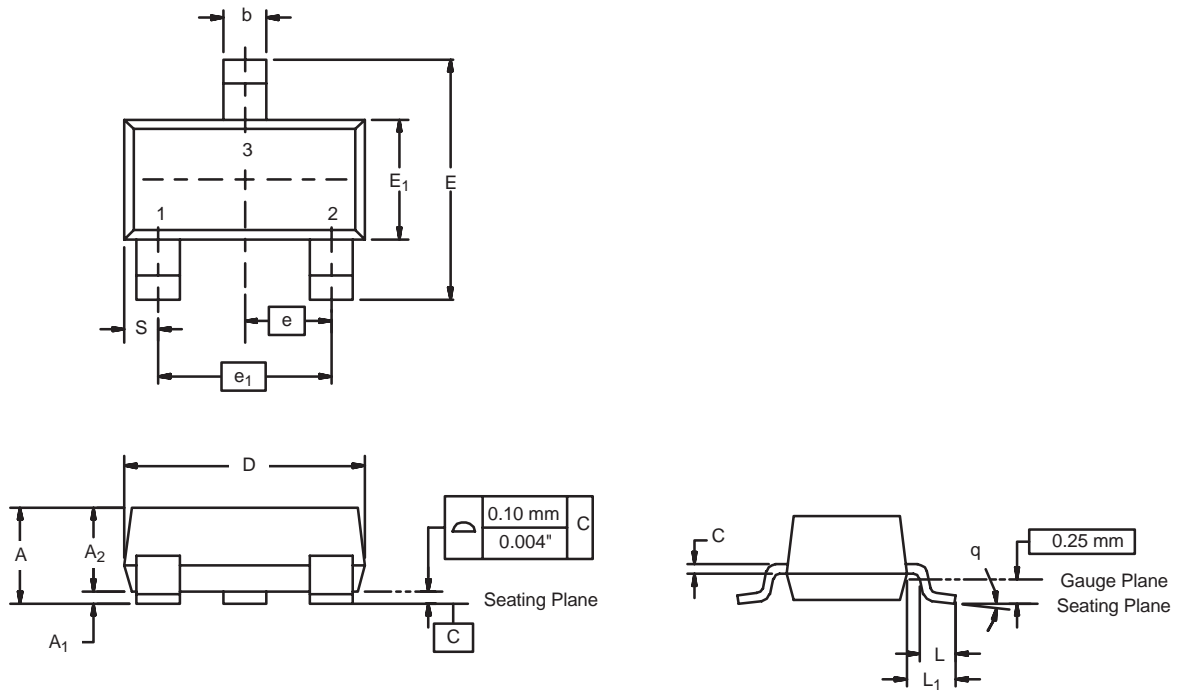
Single Pulse Power



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



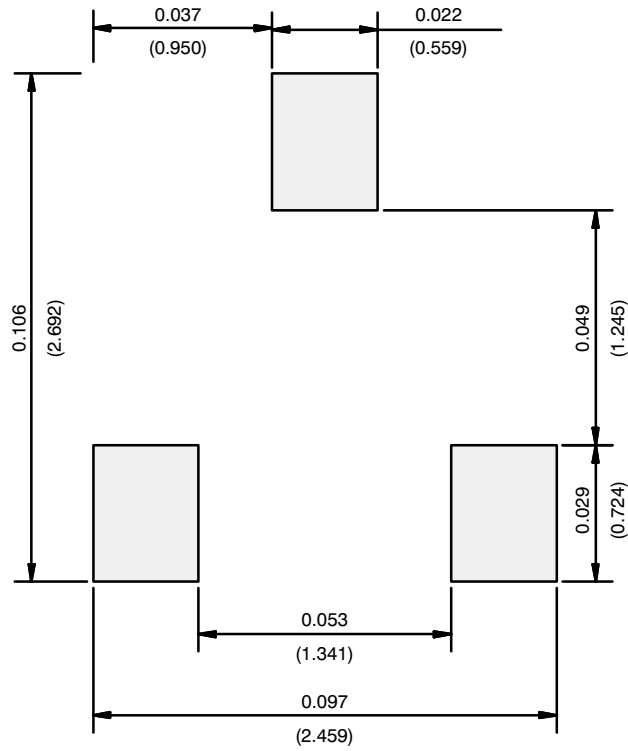
**SOT-23 (TO-236): 3-LEAD**



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A <sub>1</sub>	0.01	0.10	0.0004	0.004
A <sub>2</sub>	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E <sub>1</sub>	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e <sub>1</sub>	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L <sub>1</sub>	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01  
DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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